NSN 5961-01-290-8850

Unitized Semiconductor Devices - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5961-01-290-8850 **Inclosure Material:** Ceramic **Overall Length:** 0.785 inches **Terminal Length:** 0.260 inches **Overall Height:** 0.140 inches **Overall Width:** 0.310 inches **Component Name And Quantity:** 4 transistor **Mounting Method: Terminal Features Provided:** Quality assurance level txv **Semiconductor Material:** Silicon all transistor Voltage Rating In Volts Per Characteristic: 60.0 collector to base voltage/static/emitter open all transistor and 60.0 collector to emitter voltage/static/base open all transistor and -5.0 emitter to base voltage, static, collector open all transistor **Current Rating Per Characteristic:** 600.00 milliamperes source cutoff current all transistor **Power Rating Per Characteristic:** 1.5 watts small-signal input power, common-collector preset all transistor **Transfer Ratio:** 50.0 static forward current transfer ratio, common-emitter all transistor **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** All transistor junction pattern arrangement: pnp **Test Data Document:** 81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Terminal Type And Quantity:** 14 pin **Specification Data:** 81349-mil-s-19500/558 government specification

Demilitarization:

Unit Of Measure:

Shelf Life:

N/a

NSN 5961-01-290-8850

Unitized Semiconductor Devices - Page 2 of 2



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